

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	22mΩ@-4.5V	6A
	30mΩ@-2.5V	
-20V	50mΩ@4.5V	-5A
	70mΩ@2.5V	

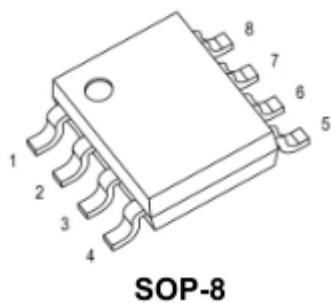
Feature

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Fast Switching Speed

Applications

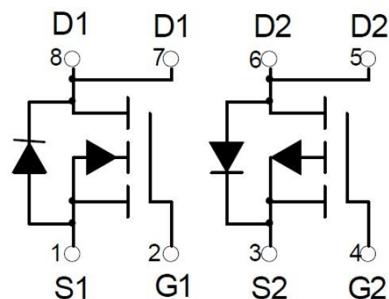
- Motor Control
- Power Management Functions
- DC-DC Converters
- Backlighting

Package

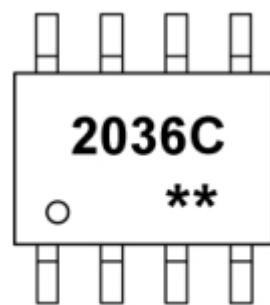


SOP-8

Circuit diagram



Marking



2036C: Product code
** : Week code.

Maximum Ratings-Total Device

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Storage Temperature	T_{STG}	-55~ +150	°C

Maximum Ratings - N-Channel Q1

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	6	A



ZL MOSFET

ZL2036C

Maximum Ratings - P-Channel Q1

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-5	A

Thermal Characteristics

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	277	$^\circ\text{C}/\text{W}$

Electrical characteristics - N-Channel Q1

($T_A=25^\circ\text{C}$, unless otherwise noted)

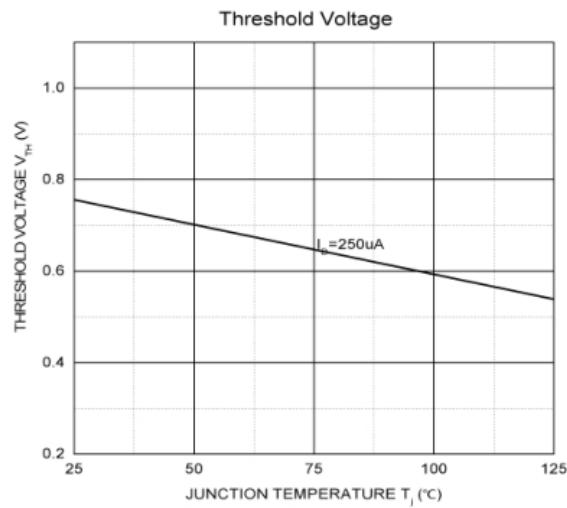
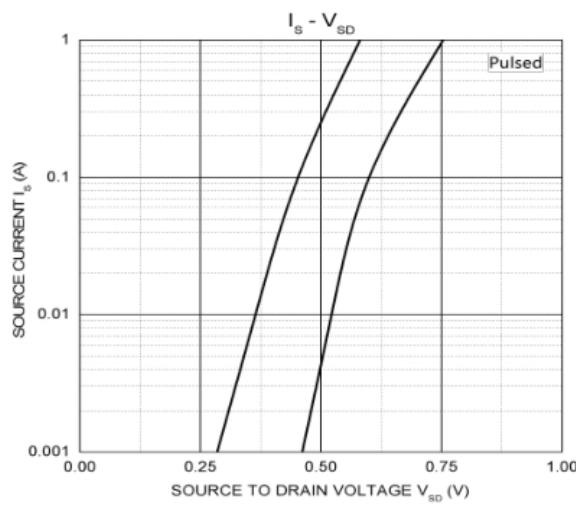
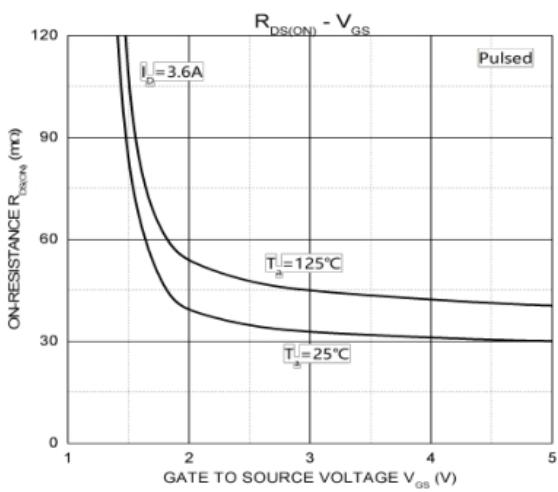
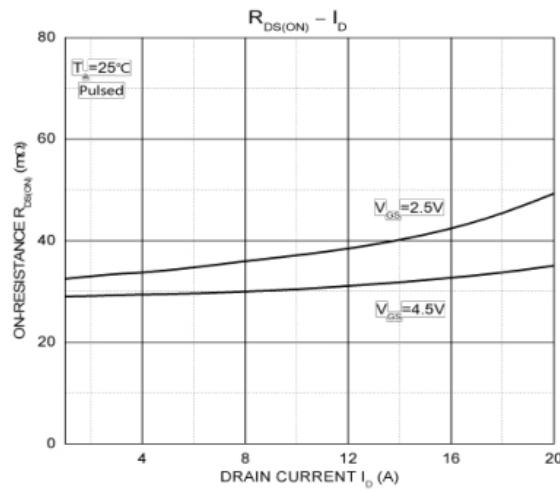
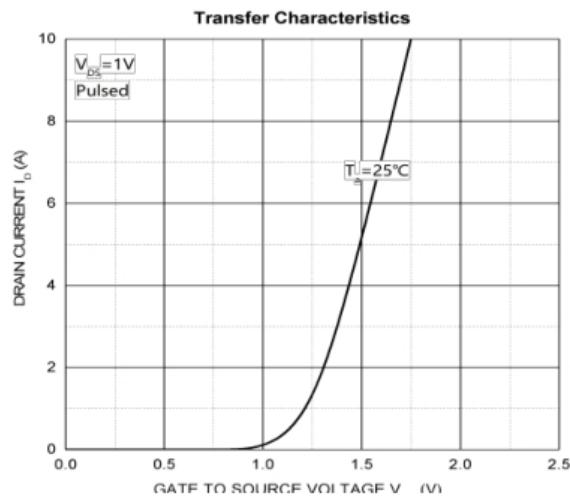
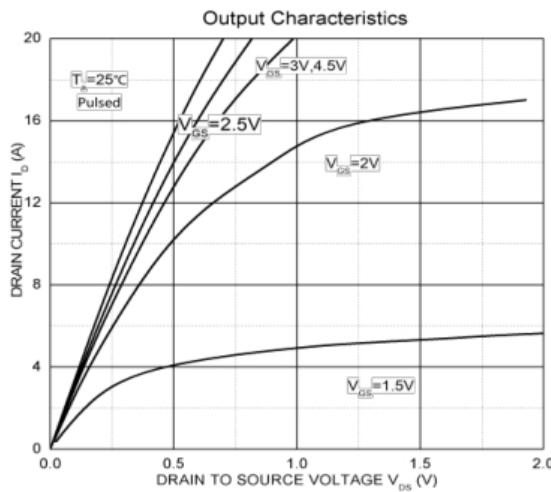
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$			± 0.1	μA
Gate threshold voltage ⁽¹⁾	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.5	0.7	1	V
Drain-source on-resistance	$R_{DS(\text{on})}$	$V_{GS} = 4.5\text{V}, I_D = 4\text{A}$		22	30	$\text{m}\Omega$
		$V_{GS} = 2.5\text{V}, I_D = 3\text{A}$		30	40	
Dynamic Characteristics						
Total gate charge	Q_g	$V_{DS} = 10\text{V}, V_{GS} = 4.5\text{V}, I_D = 4\text{A}$		11		nC
Gate-source charge	Q_{gs}			2.3		
Gate-drain charge	Q_{gd}			2.5		
Input capacitance	C_{iss}	$V_{DS} = 8\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		800		pF
Output capacitance	C_{oss}			155		
Reverse transfer capacitance	C_{rss}			125		
Switching Characteristics						
Turn-on Delay Time	$T_{d(\text{on})}$	$V_{DD} = 10\text{V}, V_{GS} = 4\text{V}, I_D = 1\text{A}, R_{\text{GEN}} = 10\Omega$		18		nS
Turn-on Rise Time	T_r			5		
Turn-Off Delay Time	$T_{d(\text{off})}$			43		
Turn-Off Fall Time	t_f			20		
Source-Drain Diode Characteristics						
Diode forward voltage	V_{SD}	$I_s = 1\text{A}, V_{GS} = 0\text{V}$			1.3	V

Electrical characteristics - P-Channel Q2

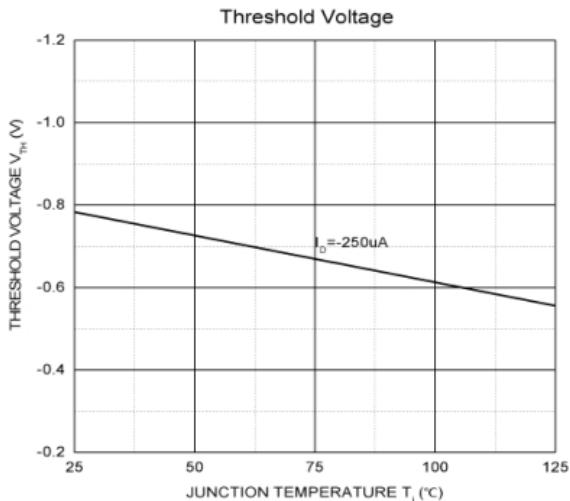
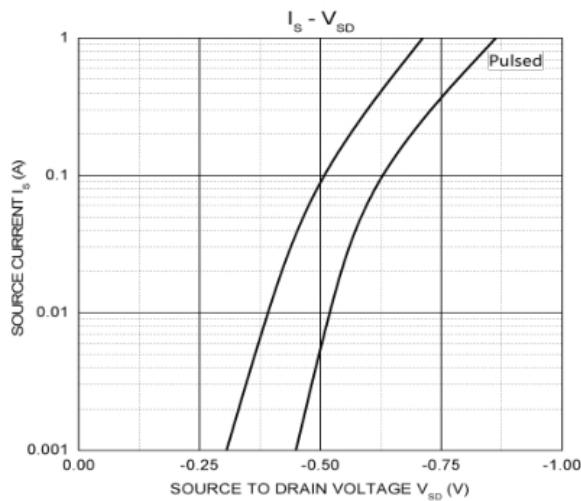
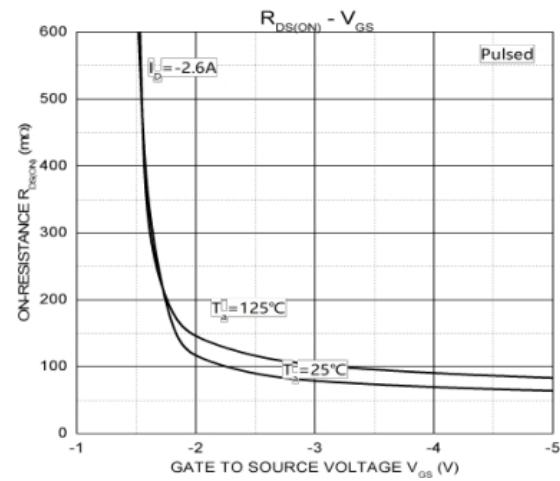
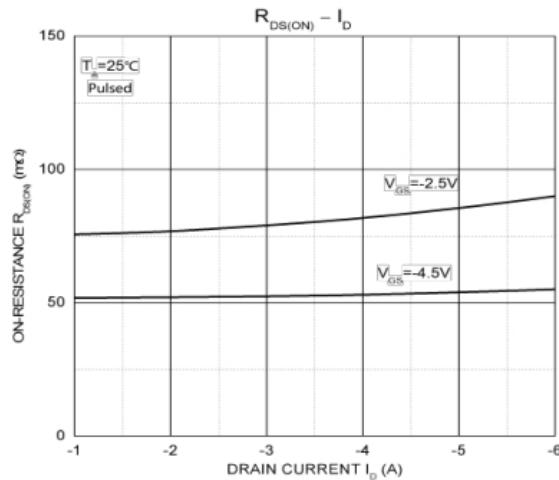
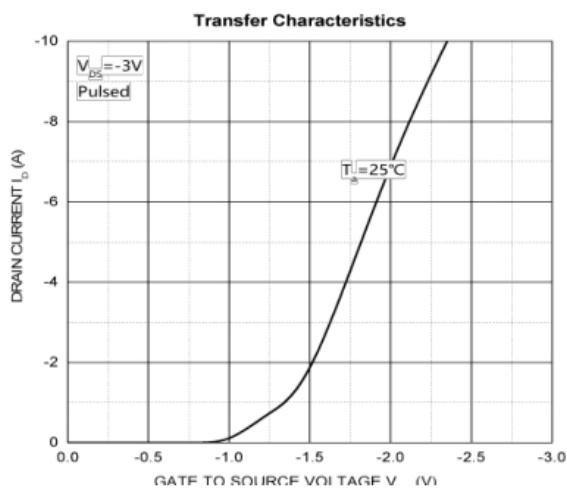
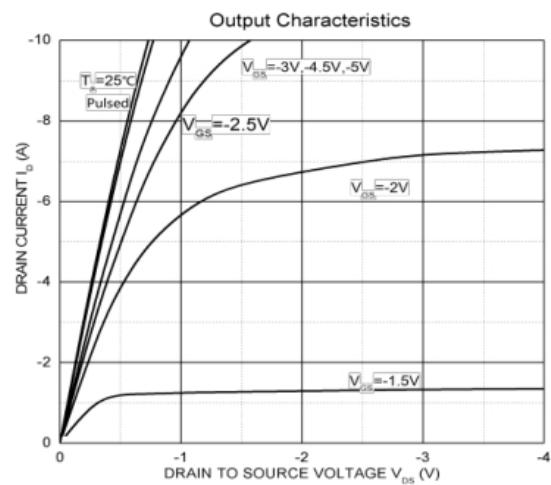
($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$			± 100	μA
Gate threshold voltage ⁽¹⁾	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-0.5	-0.7	-1	V
Drain-source on-resistance ⁽¹⁾	$R_{DS(\text{on})}$	$V_{GS} = -4.5\text{V}, I_D = -3\text{A}$		50	60	Ω
		$V_{GS} = -2.5\text{V}, I_D = -1\text{A}$		70	90	
Dynamic Characteristics²⁾						
Input capacitance	C_{iss}	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		405		pF
Output capacitance	C_{oss}			75		
Reverse transfer capacitance	C_{rss}			55		
Gate resistance	R_g	$f = 1\text{MHz}$		6		Ω
Total gate charge	Q_g	$V_{DS} = -10\text{V}, V_{GS} = -2.5\text{V}, I_D = -3\text{A}$		3.3	12	nC
Gate-source charge	Q_{gs}			0.7		
Gate-drain charge	Q_{gd}			1.3		
Turn-on Delay Time	$T_{d(on)}$	$V_{DS} = -10\text{V}, V_{GEN} = -4.5\text{V}, I_D = -1\text{A}, R_{GEN} = 1\Omega$		11		nS
Turn-on Rise Time	T_r			35		
Turn-Off Delay Time	$T_{d(off)}$			30		
Turn-Off Fall Time	t_f			10		
Source-Drain Diode Characteristics						
Diode Forward voltage	V_{SD}	$I_S = -1\text{A}, V_{GS} = 0\text{V}$			-1.3	V

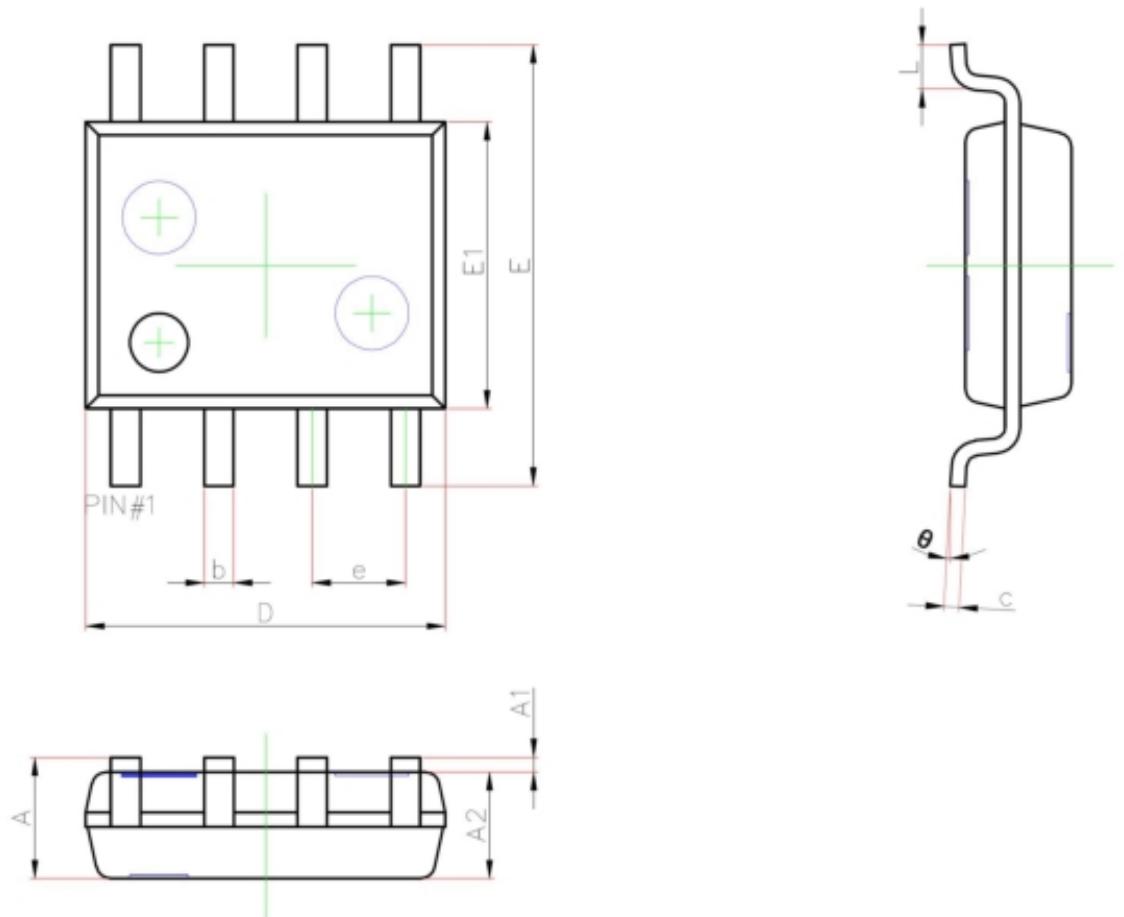
Typical Characteristics - N-Channel Q1



Typical Characteristics - P-Channel Q2



SOP-8 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°